Anisotropic and Sub-micrometric InGaP Plasma Etching for High Efficiency Photovoltaics

Alison Clarke, *Mathieu de Lafontaine, Richard R. King, Christiana B. Honsberg, and Karin Hinzer*

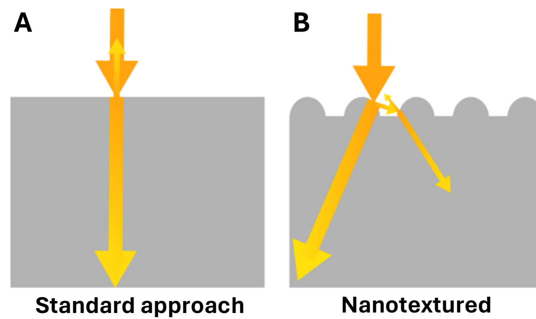

Fig. 1: Schematics of light incident on A) an untextured surface and light trapping on B) a nanotextured surface.

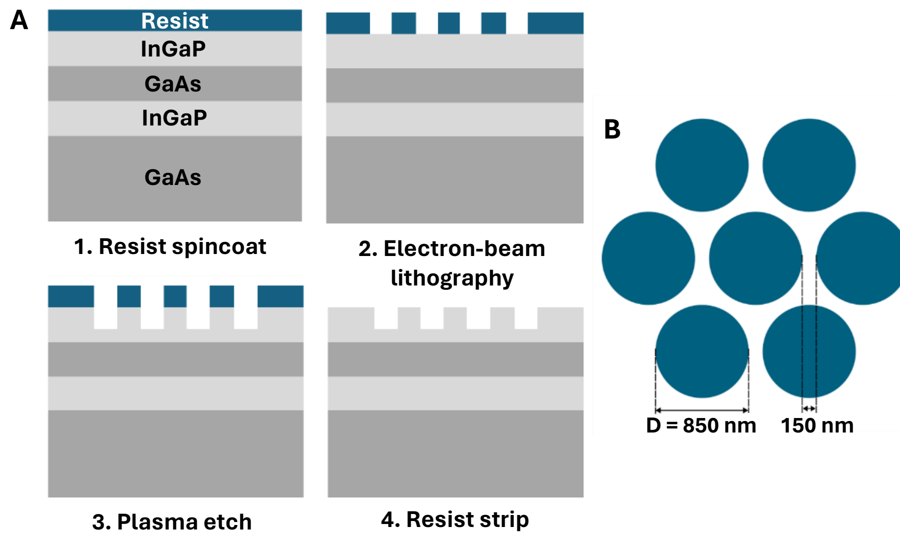

Fig. 2. A) Fabrication process flow. The grey is the III-V heterostructure and the blue is resist. B) Nanotexture pattern design. The blue area is masked and the white area is etched.

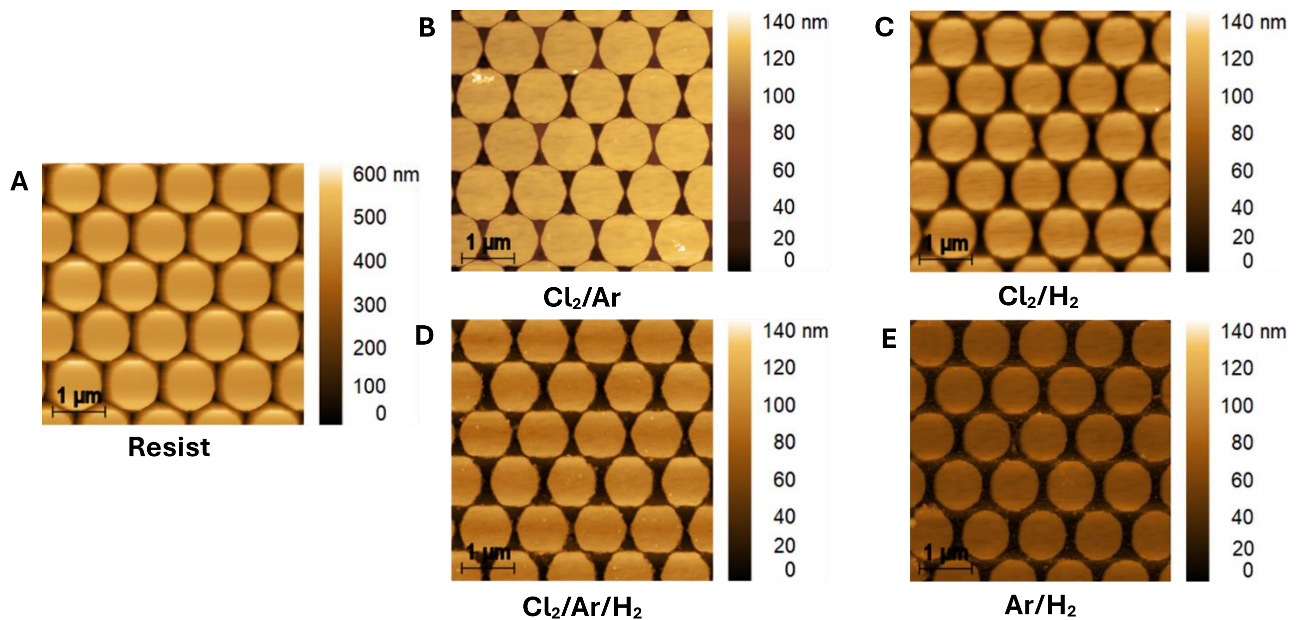

Fig. 3. AFM images of A) resist patterning after lithography and etched nanotextures using B) Cl_2/Ar, C) Cl_2/H_2, D) $Cl_2/Ar/H_2$, and E) Ar/H_2 plasma chemistries.